Ordering number:EN3150

PNP/NPN Epitaxial Planar Silicon Transistors

2SB1450/2SD2199

50V/7A Switching Applications

Features

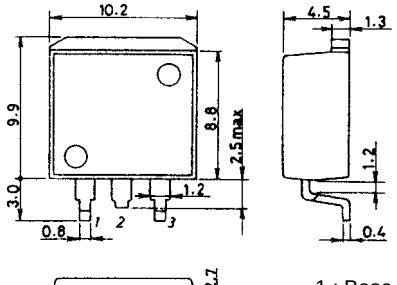
- Surface mount type device making the following possible.
  - -Reduction in the number of manufacturing processes for 2SB1450/2SD2199-applied equipment.
  - -High density surface mount applications.
  - -Small size of 2SB1450/2SD2199-applied equipment.
- Low collector-to-emitter saturation voltage.
- Highly resistant to breakdown because of wide ASO.

Package Dimensions

unit:mm

2069B

[2SB1450/2SD2199]



1 : Base
2 : Collector
3 : Emitter
SANYO : SMP-FD

( ) : 2SB1450

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(–)60	V
Collector-to-Emitter Voltage	V_{CEO}		(–)50	V
Emitter-to-Base Voltage	V_{EBO}		(–)6	V
Collector Current	I_C		(–)7	A
Collector Current (Pulse)	I_{CP}		(–)12	A
Collector Dissipation	P_C		1.65	W
		Tc=25˚C	40	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(–)40V, I_E=0			(–)0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(–)4V, I_C=0			(–)0.1	mA
DC Current Gain	$h_{FE}1$	V_{CE}=(–)2V, I_C=(–)1A	70*		280*	
	$h_{FE}2$	V_{CE}=(–)2V, I_C=(–)5A	30			
Gain-Bandwidth Product	f_T	V_{CE}=(–)5V, I_C=(–)1A		10		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=(–)4A, I_B=(–)0.4A			(–)0.4	V

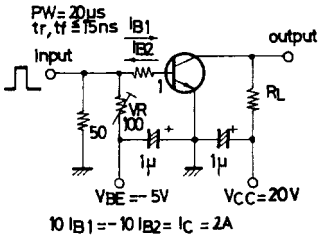
* : The 2SB1450/2SD2199 are classified by 1A h_{FE} as follows :

70	Q	140	100	R	200	140	S	280

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(–)1mA, I_E=0	(–)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(–)1mA, R_{BE}=∞	(–)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(–)1mA, I_C=0	(–)6			V
Turn-ON Time	t_{on}	See specified test circuit.		0.2		μs
Storage Time	t_{stg}	See specified test circuit.		(0.1)		μs
				0.3		μs
Fall Time	t_f	See specified test circuit.		(0.7)		μs
				0.9		μs

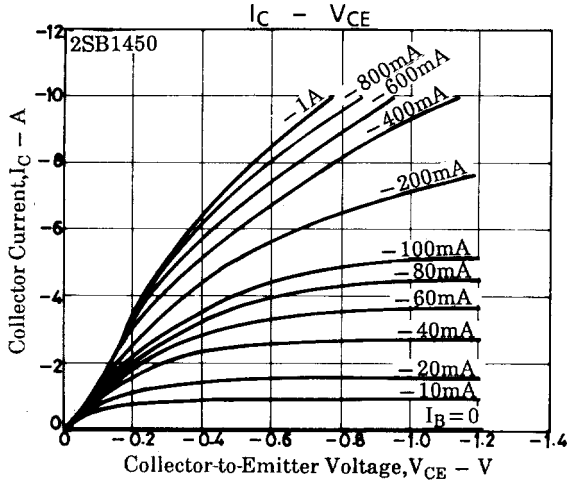
Switching Time Test Circuit

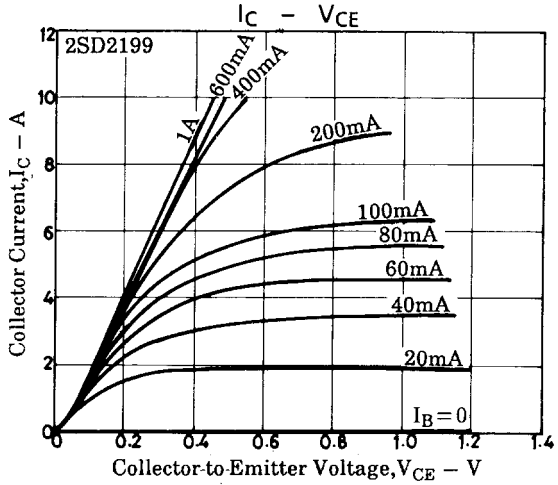


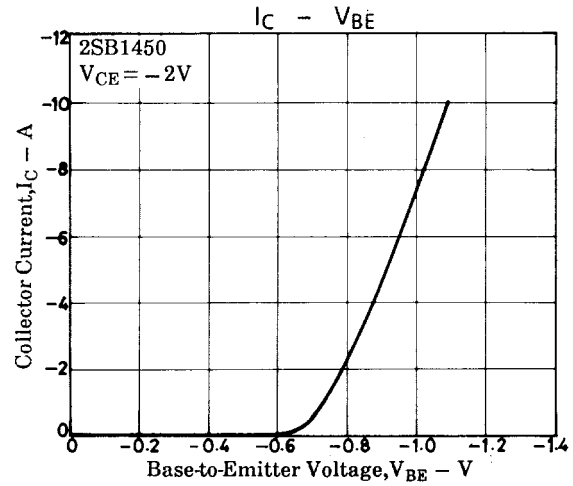
10 I_{B1} = –10 I_{B2} = I_C = 2A

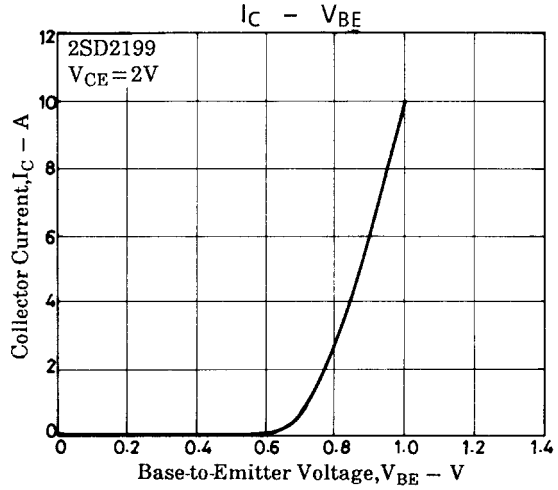
For PNP, the polarity is reversed.

Unit (resistance : Ω, capacitance : F)

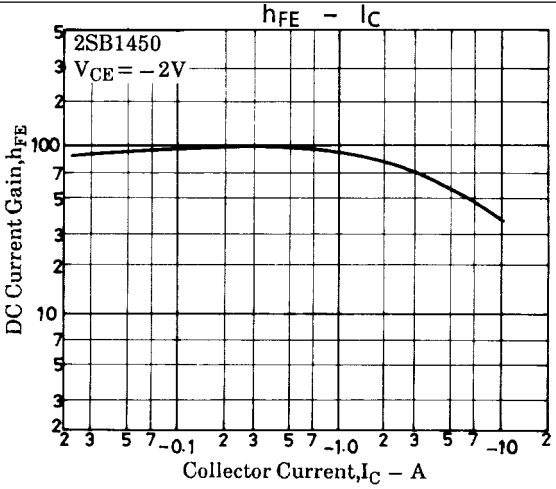




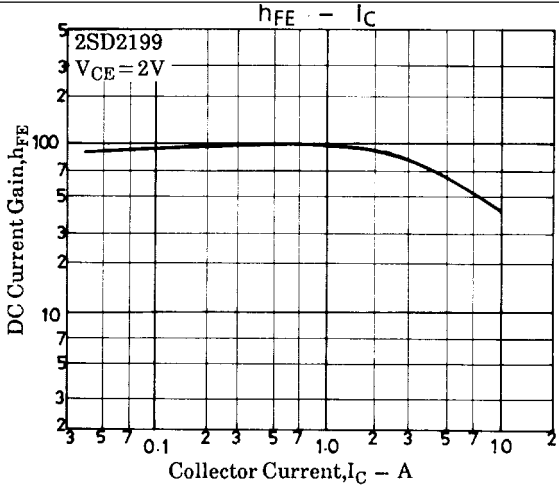




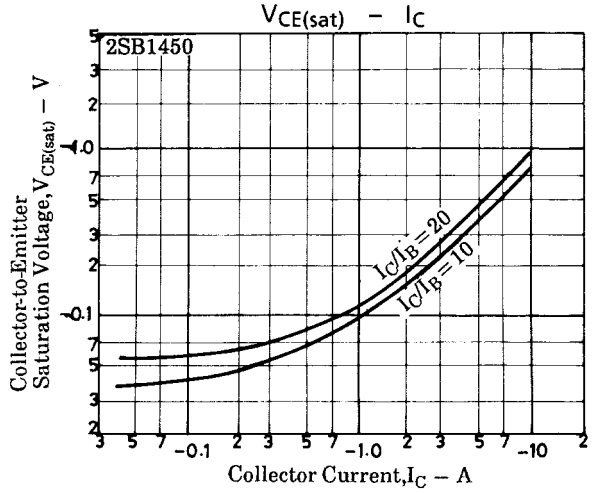
h_{FE} – I_C



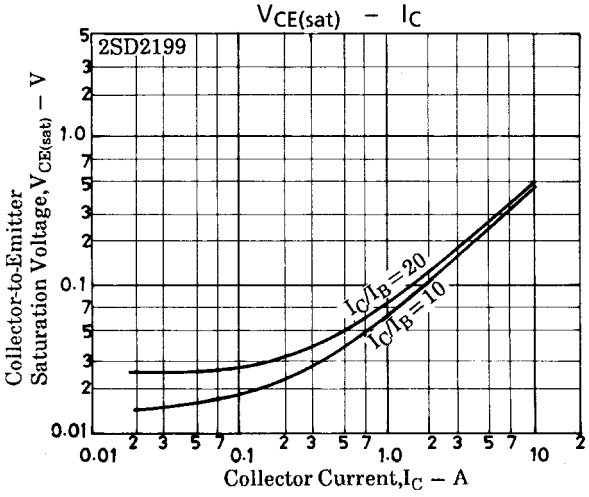
h_{FE} – I_C



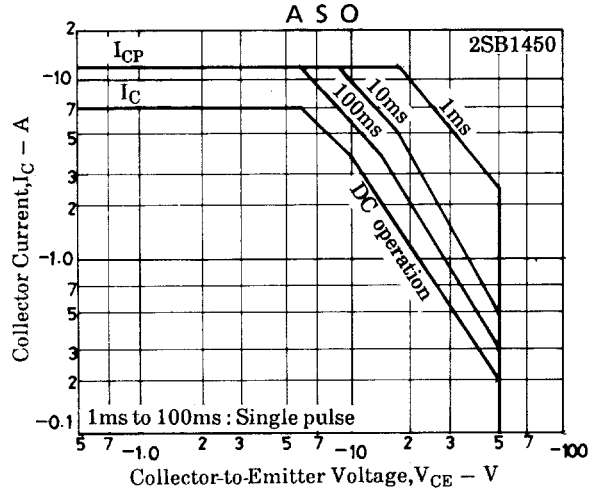
$V_{CE(sat)}$ – I_C



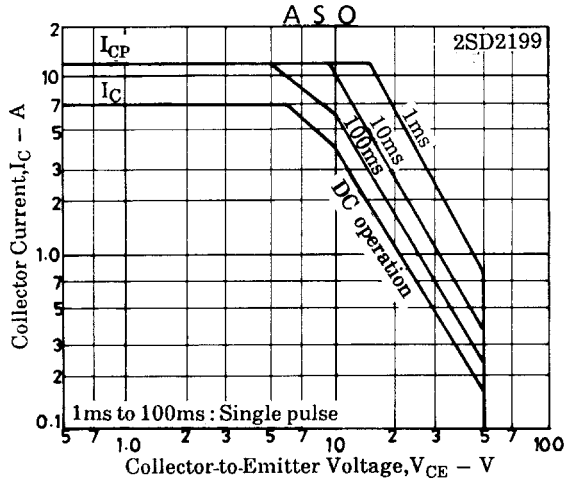
$V_{CE(sat)}$ – I_C



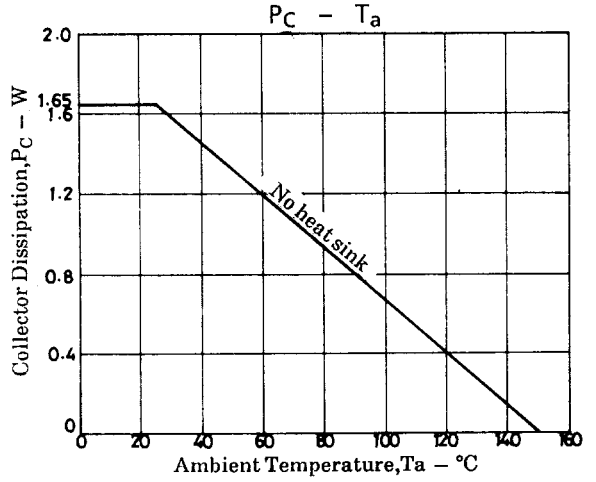
A S O



A S O



P_C – T_a



P_C – T_c